# **PC929 Series**

High Speed, Built-in Short Protection Circuit, Gate Drive SMD 14 pin \*OPIC Photocoulper



# Description

**PC929 Series** contains an IRED optically coupled to an OPIC chip.

It is packaged in a Mini-flat, Half pitch type (14 pin).

Input-output isolation voltage(rms) is 4.0kV. High speed responce (t\_{PLH}, t\_{PHL} : MAX. 0.5  $\mu s).$ 

# Features

- 1. 14 pin Half pitch type (Lead pitch : 1.27 mm)
- 2. Double transfer mold package (Ideal for Flow Soldering)
- 3. Built-in IGBT shortcircuit protector circuit
- 4. Built-in direct drive circuit for IGBT drive (Peak output current : I<sub>01P</sub>, I<sub>02P</sub> : MAX. 0.4 A)
- 5. High speed responce (t<sub>PLH</sub>, t<sub>PHL</sub> : MAX. 0.5 µs)
- 6. High isolation voltage (V<sub>iso(rms)</sub> : 4.0 kV)

# Agency approvals/Compliance

- 1. Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. **PC929**)
- 2. Approved by VDE (VDE0884) (as an option) file No. 94626 (as model No. **PC929**)
- 3. Package resin : UL flammability grade (94V-0)

# Applications

1. Inverter

\* "OPIC"(Optical IC) is a trademark of the SHARP Corporation. An OPIC consists of a light-detecting element and a signal-processing circuit integrated onto a single chip.

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#### Internal Connection Diagram



# Truth table

Input	C input-output	O <sub>2</sub> output	FS output	
ON	Low level	High level	High level	
ON	High level	Low level	Low level	At operating protection function
OFF	Low level	Low level	High level	
	High level	Low level	High level	

# Outline Dimensions

(Unit : mm)



Product mass : approx. 0.47g



# Date code (2 digit)

	1st o	digit		2nd digit		
	Year of p	roduction		Month of production		
A.D.	Mark	A.D	Mark	Month	Mark	
1990	A	2002	Р	January	1	
1991	В	2003	R	February	2	
1992	C	2004	S	March	3	
1993	D	2005	Т	April	4	
1994	Е	2006	U	May	5	
1995	F	2007	V	June	6	
1996	Н	2008	W	July	7	
1997	J	2009	Х	August	8	
1998	K	2010	А	September	9	
1999	L	2011	В	October	0	
2000	М	2012	С	November	N	
2001	N	:	:	December	D	

repeats in a 20 year cycle

Country of origin Japan

#### ■ Absolute Maximum Ratings (unless otherwise specified T - T)

(unless otherwise specified $T_a=T_{opr}$ )							
	Parameter	Symbol	Rating	Unit			
Input	*1Forward current	I <sub>F</sub>	20	mA			
Inj	<sup>*2</sup> Reverse voltage	VR	6	V			
	Supply voltage	V <sub>CC</sub>	35	V			
	O <sub>1</sub> output current	I <sub>O1</sub>	0.1	А			
	<sup>*3</sup> O <sub>1</sub> peak output current	I <sub>O1P</sub>	0.4	А			
	O <sub>2</sub> output current	I <sub>O2</sub>	0.1	А			
nt	*3O <sub>2</sub> peak output current	I <sub>O2P</sub>	0.4	А			
Output	O <sub>1</sub> output voltage	V <sub>01</sub>	35	V			
0	<sup>*4</sup> Power dissipation	Po	500	mW			
	Overcurrent detection voltage	Vc	V <sub>CC</sub>	V			
	Overcurrent detection current	I <sub>C</sub>	30	mA			
	Error signal output voltage	V <sub>FS</sub>	V <sub>CC</sub>	V			
	Error signal output current	I <sub>FS</sub>	20	mA			
*5Total power dissipation		P <sub>tot</sub>	550	mW			
*6Isolation voltage		V <sub>iso (rms)</sub>	4.0	kV			
Operating temperature		T <sub>opr</sub>	-25 to +80	°C			
Storage temperature		T <sub>stg</sub>	-55 to +125	°C			
*75	Soldering temperature	T <sub>sol</sub>	260	°C			

\*1 The derating factors of a absolute maximum ratings due to ambient temperature are shown in Fig.15

\*2  $T_a = 25^{\circ}C$ 

\*3 Pulse width≤0.15µs, Duty ratio : 0.01

\*4.5 The derating factors of a absolute maximum ratings due to ambient temperature are shown in Fig.16

AC for 1minute, 40 to 60 %RH, T<sub>a</sub>=25°C, f=60Hz \*6

\*7 For 10s

# ■ Electro-optical Characteristics

Electro-optical Characteristics					(unless otherwise specified T <sub>a</sub> =T <sub>opr</sub> )		
	Parameter Symbol Conditions *8			MIN.	TYP.	MAX.	Unit
	Forward voltage	V <sub>F1</sub>	$T_a=25^{\circ}C, I_F=10mA$	-	1.6	1.75	V
Input	Forward voltage	V <sub>F2</sub>	$T_a=25^{\circ}C, I_F=0.2mA$	1.2	1.5	-	V
Int	Reverse current	IR	$T_a=25^{\circ}C, V_R=5V$	_	_	10	μΑ
	Terminal capacitance	Ct	$T_a=25^{\circ}C$ , V=0, f=1kHz	-	30	250	pF
	Supply voltage	V <sub>CC</sub>	$T_a = -10$ to $+60^{\circ}C$	15	-	30	V
			_	15	_	24	V
	O1 Low level output voltage	V <sub>O1L</sub>	$V_{O1L}$ V <sub>CC1</sub> =12V, V <sub>CC2</sub> =-12V, I <sub>O1</sub> =0.1A, I <sub>F</sub> =5mA*9		0.2	0.4	V
	O <sub>2</sub> High level output voltage	V <sub>O2H</sub>	$V_{CC}=V_{O1}=24V, I_{O2}=-0.1A, I_F=5mA *9$	20	22	-	V
Output	O <sub>2</sub> Low level output voltage	V <sub>O2L</sub>	$V_{CC}=24V, I_{O2}=0.1A, I_{F}=0$ *9	-	1.2	2.0	V
Out	O <sub>1</sub> leak current	I <sub>O1L</sub>	$T_a=25^{\circ}C, V_{CC}=V_{O1}=35V, I_F=0 *9$	-	-	500	μΑ
	High layel supply summent	I <sub>CCH</sub>	$T_a=25^{\circ}C, V_{CC}=V_{O1}=24V, I_F=5mA*9$	-	10	17	mA
	High level supply current		$V_{CC}=V_{O1}=24V, I_F=5mA$ *9	-	-	19	mA
	Low lovel supply surrent	I <sub>CCL</sub>	$T_a=25^{\circ}C, V_{CC}=V_{O1}=24V, I_F=0$ *9	_	11	18	mA
	Low level supply current		$V_{CC}=V_{O1}=24V, I_F=0$ *9	_	_	20	mA

\*8 It shall connect a by-pass capacitor of 0.01 µF or more between V<sub>CC</sub> (pin (3)) and GND (pin, (0), (4)) near the device, when it measures the transfer characteristics and the output side characteristics. \*9 FS=OPEN, V<sub>C</sub>=0

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					(unless	otherwis	e specified	1 T <sub>a</sub> =T <sub>opr</sub> )
		Parameter	Symbol	Conditions <sup>*10</sup>	MIN.	TYP.	MAX.	Unit
	*11	<sup>1</sup> "Low $\rightarrow$ High" input threshold current	I <sub>FLH</sub>	$T_a=25^{\circ}C, V_{CC}=V_{O1}=24V, FS=OPEN, V_C=0$	0.3	1.5	3.0	mA
		Low-ringh input threshold current		$V_{CC}=V_{O1}=24V$ , FS=OPEN, Vc=0	0.2	-	5.0	mA
	Isolation resistance		R <sub>ISO</sub>	$T_a=25^{\circ}C$ , DC=500V, 40 to 60%RH	5×10 <sup>10</sup>	1011	-	Ω
ics	ime	"Low→High" propagation delay time	t <sub>PLH</sub>	$T_a=25^{\circ}C,$	-	0.3	0.5	μs
srist	Response time	"High→Low" propagation delay time	t <sub>PHL</sub>	$V_{CC}=V_{O1}=24V, I_{F}=5mA,$	-	0.3	0.5	μs
acte	bon	Rise time	t <sub>r</sub>	$R_G=47\Omega, C_G=3\ 000pF$	-	0.2	0.5	μs
char	Re	Fall time	t <sub>f</sub>	FS=OPEN, $V_C=0$	-	0.2	0.5	μs
Transfer characteristics		Instantaneous common mode rejection voltage (High level output)	CM <sub>H</sub>	$T_{a}=25^{\circ}C, V_{CM}=600V(p-p)$ I <sub>F</sub> =5mA, V <sub>CC</sub> =V <sub>01</sub> =24V, $\Delta V_{02H}=2.0V, FS=OPEN, V_{C}=0$	-1.5	-	-	kV/μs
		Instantaneous common mode rejection voltage (Low level output)	CML	$T_{a}=25^{\circ}C, V_{CM}=600V(p-p)$ $I_{F}=0, V_{CC}=V_{O1}=24V,$ $\Delta V_{O2L}=2.0V, FS=OPEN, V_{C}=0$		-	_	kV/µs
Overcurrent detection	*12 Overcurrent detection voltage V <sub>C1</sub>		V <sub>CTH</sub>	$T_a=25^{\circ}C$ $V_{CC}=V_{O1}=24V$	V <sub>CC</sub> -6.5	V <sub>CC</sub> -6	V <sub>CC</sub> -5.5	V
Overc detec		Overcurrent detection voltage hysteresis width	V <sub>CHIS</sub>	$I_F=5mA$ , $R_G=47\Omega$ $C_G=3$ 000pF, FS=OPEN	1	2	3	V
utput		O <sub>2</sub> "High→Low" propagation delay time at overcurrent protection	t <sub>PCOHL</sub>	$T_a=25^{\circ}C$ $V_{CC}=V_{O1}=24V$	-	4	10	μs
Protection output		O <sub>2</sub> Fall time at overcurrent protection	t <sub>PCOtf</sub>	$I_{F}=5mA$ , $R_{G}=47\Omega$ , $C_{G}=3$ 000pF,	2	5	-	μs
Prote		$O_2$ "High $\rightarrow$ Low" output voltage at overcurrent protection	V <sub>OE</sub>	R <sub>C</sub> =1kΩ, C <sub>P</sub> =3 000pF FS=OPEN	-	_	2	V
ut		Low level error signal voltage	V <sub>FSL</sub>	$T_a=25^{\circ}C, I_F=5mA$ $V_{CC}=V_{O1}=24V$ $I_{FS}=10mA, R_G=47\Omega$ $C_G=3\ 000pF, C=OPEN$	_	0.2	0.4	V
Error signal output		High level error signal voltage	I <sub>FSH</sub>	$T_{a}=25^{\circ}C$ $V_{CC}=V_{01}=24V, I_{F}=5mA$ $V_{FS}=24V, R_{G}=47\Omega$ $C_{G}=3\ 000pF, V_{C}=0$	_	-	100	μΑ
Er		Error signal "High→Low" propagation delay time	t <sub>PCFHL</sub>	$T_a=25^{\circ}C, V_{CC}=V_{O1}=24V$ $I_F=5mA, R_{FS}=1.8k\Omega$	_	1	5	μs
		Error signal output pulse width	$\Delta t_{FS}$	$\label{eq:rescaled} \begin{array}{l} R_{\rm G} = 47\Omega, \ R_{\rm C} = 1 k\Omega \\ C_{\rm G} = 3 \ 000 \mbox{pF}, \ C_{\rm P} = 1 \ 000 \mbox{pF} \end{array}$	20	35	-	μs

<sup>1</sup>10 It shall connect a by-pass capacitor of 0.01 μF or more between V<sub>CC</sub> (pin ③) and GND (pin ④, ④) near the device, when it measures the device, when it measures the overcurrent characteristics, Protection output characteristics, and Error signal output characteristics.
 \*11 I<sub>FLH</sub> represents forward current when output goes from "Low" to "High"
 \*12 V<sub>CTH</sub> is the of C(pin ⑨) voltage when output becomes from "High" to "Low"



# ■ Model Line-up

Lead Form	SMT Gullwing						
Dealeaga	Sle	eve	Taping				
Package	50pcs/	/sleeve	1 000pcs/reel				
VDE0884	—— Approved			Approved			
Model No.	PC929	PC929Y	PC929P	PC929PY			

Please contact a local SHARP sales representative to inquire about production status and Lead-Free options.



Fig.1 Test Circuit for O<sub>1</sub> Low Level Output Voltage



Fig.3 Test Circuit for O<sub>2</sub> Low Level Output Voltage



Fig.5 Test Circuit for "Low→High" Input Threshold Current



Fig.2 Test Circuit for O<sub>2</sub> High Level Output Voltage



Fig.4 Test Circuit for O1 Leak Current



Fig.6 Test Circuit for High Level / Low Level Supply Current



# Fig.7 Test Circuit for Instantaneous Common Mode Rejection Voltage

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Fig.9 Test Circuit for Overcurrent Detection Voltage, Overcurrent Detection Voltage Hysteresis



Fig.10 Test Circuit for O<sub>2</sub> Output Voltage at Overcurrent Protection





Fig.11 Test Circuit for O1 Low Level Error Signal Voltage



Fig.12 Test Circuit for High Level Error Signal Current



Fig.13 Test Circuit for O<sub>2</sub> "High→Low" Propagation Delay Time at Overcurrent Protection, O<sub>2</sub> Fall Time at Overcurrent Protection



Fig.14 Error Signal "High→Low" propagation Delay Time, Error Signal Output Pulse Width





# Fig.15 Forward Current vs. Ambient Temperature











#### Fig.16 Power Dissipation vs. Ambient Temperature



# Fig.18 "Low→High" Relative Input Threshold Current vs. Supply Voltage



Fig.20 O<sub>1</sub> Low Level Output Voltage vs. O<sub>1</sub> Output Current



Fig.21 O<sub>1</sub> Low Level Output Voltage vs. Ambient Temperature











# Fig.22 O<sub>1</sub> Leak Current vs. Ambient Temperature



# Fig.24 O<sub>2</sub> High Level Output Voltage vs. Ambient Temperature



Fig.26 O<sub>2</sub> Low Level Output Voltage vs. Ambient Temperature





Fig.27 High Level Supply Current vs. Supply Voltage











#### Fig.28 Low Level Supply Current vs. Supply Voltage



# Fig.30 Propagation Delay Time vs. Ambient Temperature









Fig.33 Error Signal "High-Low" Propagation Delay Time vs. Ambient Temperature











# Fig.34 O<sub>2</sub> Output Voltage at Protection from Overcurrent vs. Ambient Temperature



# Fig.36 High Level Error Signal Current vs. Ambient Temperature









#### Fig.39 Overcurrent Detecting Voltage - Supply Voltage Characteristics Test Circuit



# Fig.40 Example of The Application Circuit (IGBT Drive for Inverter)



- In order to stabilize the power supply line, we recommend to locate a bypass capacitor  $C_B$  (0.01 $\mu$ F or more) between V<sub>CC</sub> and GND near photocoupler.
- In order to stabilize the detecting voltage of pin-C, we recommend to locate a capacitor C<sub>P</sub> (approximately 1 000pF) between pin-C and GND, and a resistor R<sub>C</sub> (approximately 1.0kΩ) between V<sub>CC</sub> and pin-C. However, the rise time of the detection voltage at Pin-C varies along with the time constants of C<sub>P</sub> and R<sub>C</sub>. So, please make sure the device works properly in actual conditions.
- For the diode D, which is located between pin-C and collector of IGBT, we recommend to use a diode that has the withstand voltage characteristic equivalent to IGBT and also has little leak current.
- In order to prevent the failure mode or breakdown of pin-C from V<sub>CE</sub> variation of IGBT, we recommend to locate a resistor R<sub>2</sub> (approximately 10k $\Omega$ ) and a diode D1 at near pin-C, and a resistor R<sub>3</sub> (approximately 50k $\Omega$ ) and a diode D<sub>2</sub> at between pin-C and GND.

This application circuit shows the general example of a circuit, and is not a design guarantee for right operation.



# Fig.41 Operations of Shortcircuit Protector Circuit



- 1. Detection of increase in V<sub>CE(sat)</sub> of IGBT due to overcurrent by means of C terminal (pin (9))
- 2. Reduction of the IGBT gate voltage, and suppression of the collector current
- 3. Simultaneous output of signals to indicate the shortcircuit condition (FS signal) from FS (pin (a)) terminal to the microcomputer
- 4. Judgement and processing by the microcomputer -
- → In the case of instantaneous shortcircuit, run continues.
- At fault, input to the photocoupler is cut off, and IGBT is turned OFF.

Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.



#### Design Considerations

#### Notes about static electricity

Transistor of detector side in bipolar configuration may be damaged by static electricity due to its minute design.

When handling these devices, general countermeasure against static electricity should be taken to avoid breakdown of devices or degradation of characteristics.

#### • Design guide

In order to stabilize power supply line, we should certainly recommend to connect a by-pass capacitor of  $0.01\mu$ F or more between V<sub>CC</sub> and GND near the device.

We recommed to use approximately 1 000pF of capacitor between C-pin and GND in order to prevent miss opration by noise.

In the case that capacitor is used approximately  $1k\Omega$  of resistance shall be recommended to use between V<sub>CC</sub> and C-pin However, the rise time of C-pin shall be changed by time constant of added CR, so that please use this device after confirmation.

In case that some sudden big noise caused by voltage variation is provided between primary and secondary terminals of photocoupler some current caused by it is floating capacitance may be generated and result in false operation since current may go through LED or current may change.

If the photocoupler may be used under the circumstances where noise will be generated we recommend to use the bypass capacitors at the both ends of LED.

The detector which is used in this device, has parasitic diode between each pins and GND.

There are cases that miss operation or destruction possibly may be occurred if electric potential of any pin becomes below GND level even for instant.

Therefore it shall be recommended to design the circuit that electric potential of any pin does not become below GND level.

This product is not designed against irradiation and incorporates non-coherent LED.



#### • Degradation

In general, the emission of the LED used in photocouplers will degrade over time.

In the case of long term operation, please take the general LED degradation (50% degradation over 5years) into the design consideration.

Please decide the input current which become 2times of MAX. IFLH.

# • Recommended Foot Print (reference)



(Unit : mm)

☆ For additional design assistance, please review our corresponding Optoelectronic Application Notes.



#### Manufacturing Guidelines

#### Soldering Method

**Reflow Soldering:** 

Reflow soldering should follow the temperature profile shown below. Soldering should not exceed the curve of temperature profile and time. Please don't solder more than twice.



#### Flow Soldering :

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 260°C and within 10s. Preheating is within the bounds of 100 to 150°C and 30 to 80s. Please don't solder more than twice.

#### Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C. Please don't solder more than twice.

#### Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



#### • Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below Immersion time should be 3minutes or less

#### Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

#### Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

# • Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this device.

Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform) Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.



#### Package specification

#### • Sleeve package

Package materials Sleeve : HIPS (with anti-static material) Stopper : Styrene-Elastomer

# Package method

MAX. 50 pcs. of products shall be packaged in a sleeve.Both ends shall be closed by tabbed and tabless stoppers.The product shall be arranged in the sleeve with its primary side mark on the tabless stopper side.MAX. 20 sleeves in one case.

# Sleeve outline dimensions





# • Tape and Reel package

Package materials

Carrier tape : A-PET (with anti-static material)

Cover tape : PET (three layer system)

Reel : PS

Carrier tape structure and Dimensions



Dimensions List (Unit : mn							
А	В	С	D	Е	F	G	
16.0 <sup>±0.3</sup>	$7.5^{\pm 0.1}$	$1.75^{\pm 0.1}$	$12.0^{\pm0.1}$	$2.0^{\pm 0.1}$	$4.0^{\pm 0.1}$	φ1.5 <sup>+0.1</sup>	
Н	Ι	J	K				
$10.4^{\pm 0.1}$	$0.4^{\pm 0.05}$	$4.2^{\pm 0.1}$	$9.7^{\pm 0.1}$				

Reel structure and Dimensions



I	Dimensio	ns List	(Unit : mm)			
	а	b	с	d		
	330	$17.5^{\pm 1.5}$	100 <sup>±1.0</sup>	13 <sup>±0.5</sup>		
	e	f	g			
	23 <sup>±1.0</sup>	$2.0^{\pm 0.5}$	2.0 <sup>±0.5</sup>			

# Direction of product insertion





[Packing : 1 000pcs/reel]

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- --- Personal computers
- --- Office automation equipment
- --- Telecommunication equipment [terminal]
- --- Test and measurement equipment
- --- Industrial control
- --- Audio visual equipment
- --- Consumer electronics

(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection with equipment that requires higher reliability such as:

- --- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- --- Traffic signals
- --- Gas leakage sensor breakers
- --- Alarm equipment
- --- Various safety devices, etc.

(iii) SHARP devices shall not be used for or in connection with equipment that requires an extremely high level of reliability and safety such as:

- --- Space applications
- --- Telecommunication equipment [trunk lines]
- --- Nuclear power control equipment
- --- Medical and other life support equipment (e.g., scuba).

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